

### **Features**

- Schottky-type photodiode
- Intrinsic visible blindness due to wide-bandgap semiconductor material
- Built-in filter glass for low sensitivity above 400nm
- Large photoactive area
- No focusing lens needed, therefore large usable incident angle
- Designed to operate in photovoltaic mode
- TO-46 metal package

### **Maximum Ratings**

<b>Parameter</b>	<b>Symbol</b>	<b>Value</b>	<b>Unit</b>
Operating temperature range	$T_{opt}$	-20 ... +80	°C
Reverse voltage	$V_{Rmax}$	3	V
Forward current	$I_{Fmax}$	1	mA
Total power dissipation at 25°C	$P_{tot}$	1	mW

## TW30DZ

### General Characteristics

(T<sub>a</sub> = 25 °C)

Parameter	Symbol	typ. Value	Unit
Active area	A	4.18	mm <sup>2</sup>
Active area dimensions	L x W	2.2 x 1.9	mm <sup>2</sup>
Max. viewing angle	α	app. 70	degree
Shunt resistance (dark)	R <sub>s</sub>	40	MΩ
Dark current at 10mV reverse bias	I <sub>d</sub>	30	pA
Open circuit voltage (200μW/cm <sup>2</sup> , λ=300nm)	V <sub>0</sub>	120	mV
Short circuit current (200μW/cm <sup>2</sup> , λ=300nm)	I <sub>0</sub>	160	nA
Breakdown voltage (dark)	V <sub>BR</sub>	> 3	V

### Spectral Characteristics

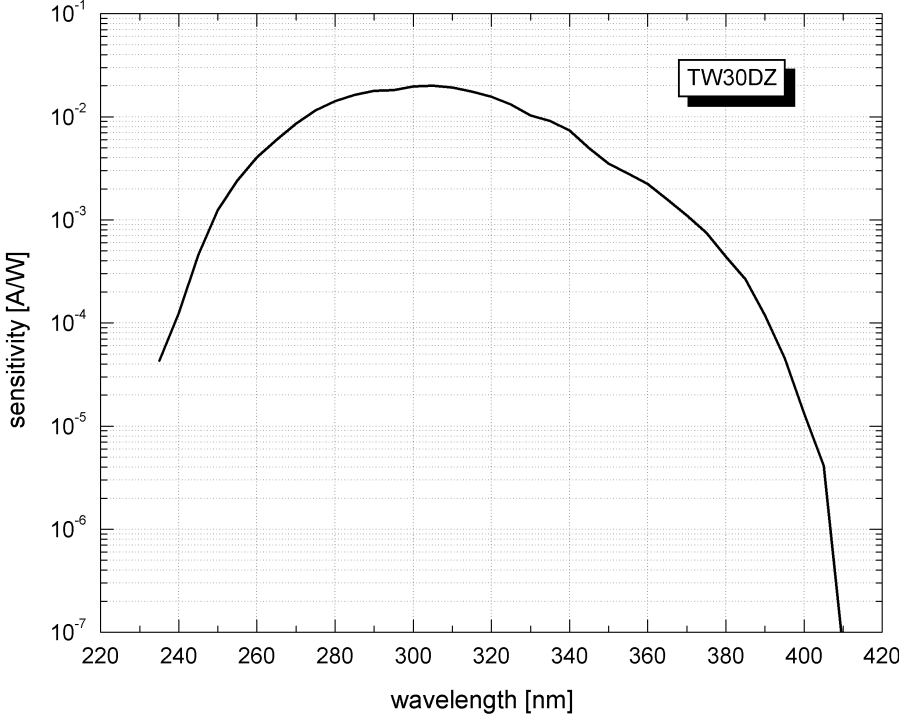
(T<sub>a</sub> = 25 °C)

Parameter	Symbol	typ. Value	Unit
Max. spectral sensitivity	S <sub>max</sub>	20	mA W <sup>-1</sup>
Wavelength of max. spectral sensitivity	λ <sub>Smax</sub>	300	nm
Range of spectral sensitivity (S=0.1*S <sub>max</sub> )	-	253-361	nm
Visible blindness	$\frac{S_{max}}{S_{400nm}}$	>1.000	

# Ultraviolet selective thin film sensor TW30DZ



## Spectral Response



## Pin Layout

